

METHODS OF FORMING INTEGRATED CIRCUITS USING MASKS TO  
PROVIDE ION IMPLANTATION SHIELDING TO PORTIONS OF A  
SUBSTRATE ADJACENT TO AN ISOLATION REGION THEREIN AND  
INTEGRATED CIRCUITS FORMED USING SAME

ABSTRACT

Methods of forming a channel region between isolation regions of an  
5 integrated circuit substrate are disclosed. In particular, a mask can be formed on an  
isolation region that extends onto a portion of the substrate adjacent to the isolation  
region to provide a shielded portion of the substrate adjacent to the isolation region  
and an exposed portion of the substrate spaced apart from the isolation region having  
the shielded portion therebetween. A channel region can be formed in the exposed  
10 portion of the substrate. Related integrated circuits are also discussed.